

ABSTRACT

A semiconductor memory device includes multiple first electrode layers stacked in a first direction, multiple second electrode layers stacked in the first direction, a first columnar body extending through the multiple first electrode layers in the first direction, a second columnar body extending through the multiple second electrode layers in the first direction, a connection part connecting the first columnar body and the second columnar body, and a spacer film having an island configuration surrounding the connection part. The multiple first electrode layers and the multiple second electrode layers are arranged in the first direction, and the connection part and the spacer film are provided between the multiple first electrode layers and the multiple second electrode layers.